Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	4.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	50	mA
				60	
I_H	I_T =500mA		MAX.	35	mA
dV/dt	V_D=540V Gate Open T_j =125		MIN.	800	V/μs
(dI/dt)c	(dV/dt)c=20V/μs T_j=125		MIN.	10	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	3	μs
t_{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =17A t_p=380μs	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.77	V
R_D	Dynamic resistance	T_j=125	35	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=125	0.5	mA

THERMAL RESISTANCES

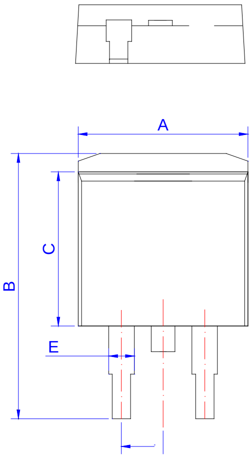
Symbol **Param9 0 Td [(P)1 (ar)3 (am)15.7DC .0 (ar)3 (ar /P <</MCID 1334**

FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature 0

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.370		0.378
D	2.40			0.094		
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033

DELIVERY MODE